L Number	Hits	Search Text	DB	Time stamp
2	1034	((In."sub.y"Ga."sub1-y"As) (In."sub.x"Ga."sub1-x"As) (Ga."sub.y"In."sub1-y"As) (Ga."sub.x"In."sub1-x"As) ("In.sub."$6"Ga.sub."$6As) ("Ga.sub."$6"In.sub."$6As) InGaAs GaInAs (indium near aluminum near arsenide)) with channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:54
4	160	(InAlAs ("In.sub."$6"Al.sub."$6As) (In."sub.y"Al."sub1-y"As) (In."sub.x"Al."sub1-x"As) (Al."sub.y"In."sub1-y"As) (Al."sub.x"In."sub1-x"As) (indium near aluminum near arsenide)) with schottky	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:57
5	90	(((In."sub.y"Ga."sub1-y"As) (In."sub.x"Ga."sub1-x"As) (Ga."sub.y"In."sub1-y"As) (Ga."sub.x"In."sub1-x"As) ("In.sub."$6"Ga.sub."$6As) ("Ga.sub."$6"In.sub."$6As) InGaAs GaInAs (indium near aluminum near arsenide)) with channel) and ((InAlAs ("In.sub."$6"Al.sub."$6As) (In."sub.y"Al."sub1-y"As) (In."sub.x"Al."sub1-x"As) (Al."sub.y"In."sub1-y"As) (Al."sub.x"In."sub1-x"As) (indium near aluminum near arsenide)) with schottky)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 11:57

L Number	Hits	Search Text	DB	Time stamp
10	83009	barrier near (film layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:23
11	18080	channel near (layer film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:24
12	1483	schottky near (layer film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:24
13	34217	bandgap (band near gap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:24
14	50	(barrier near (film layer)) and (channel near (layer film)) and (schottky near (layer film)) and (bandgap (band near gap))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/03 13:24

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